

FEATURES

- n **LOW INTERMODULATION DISTORTION** n **HIGH GAIN**
 IM3=-30 dBc at Pout= 42.0dBm G1dB=7.5dB at 5.3GHz to 5.9GHz
 Single Carrier Level
- n **HIGH POWER** n **BROAD BAND INTERNALLY MATCHED FET**
 P1dB=49.0dBm at 5.3GHz to 5.9GHz n **HERMETICALLY SEALED PACKAGE**

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset=10.0A f = 5.3 to 5.9GHz	dBm	48.0	49.0	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	6.5	7.5	—
Drain Current	IDS1		A	—	18.0	20.0
Gain Flatness	ΔG		dB	—	—	± 0.8
Power Added Efficiency	η_{add}		%	—	36	—
3rd Order Intermodulation Distortion	IM3	Two-Tone Test Po=42.0dBm	dBc	-25	-30	—
Drain Current	IDS2	(Single Carrier Level)	A	—	—	16.0
Channel Temperature Rise	ΔT_{ch}	(VDS X IDS +Pin-P1dB) X Rth(c-c)	°C	—	—	100

Recommended Gate Resistance(Rg) : 28 W (Max.)

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

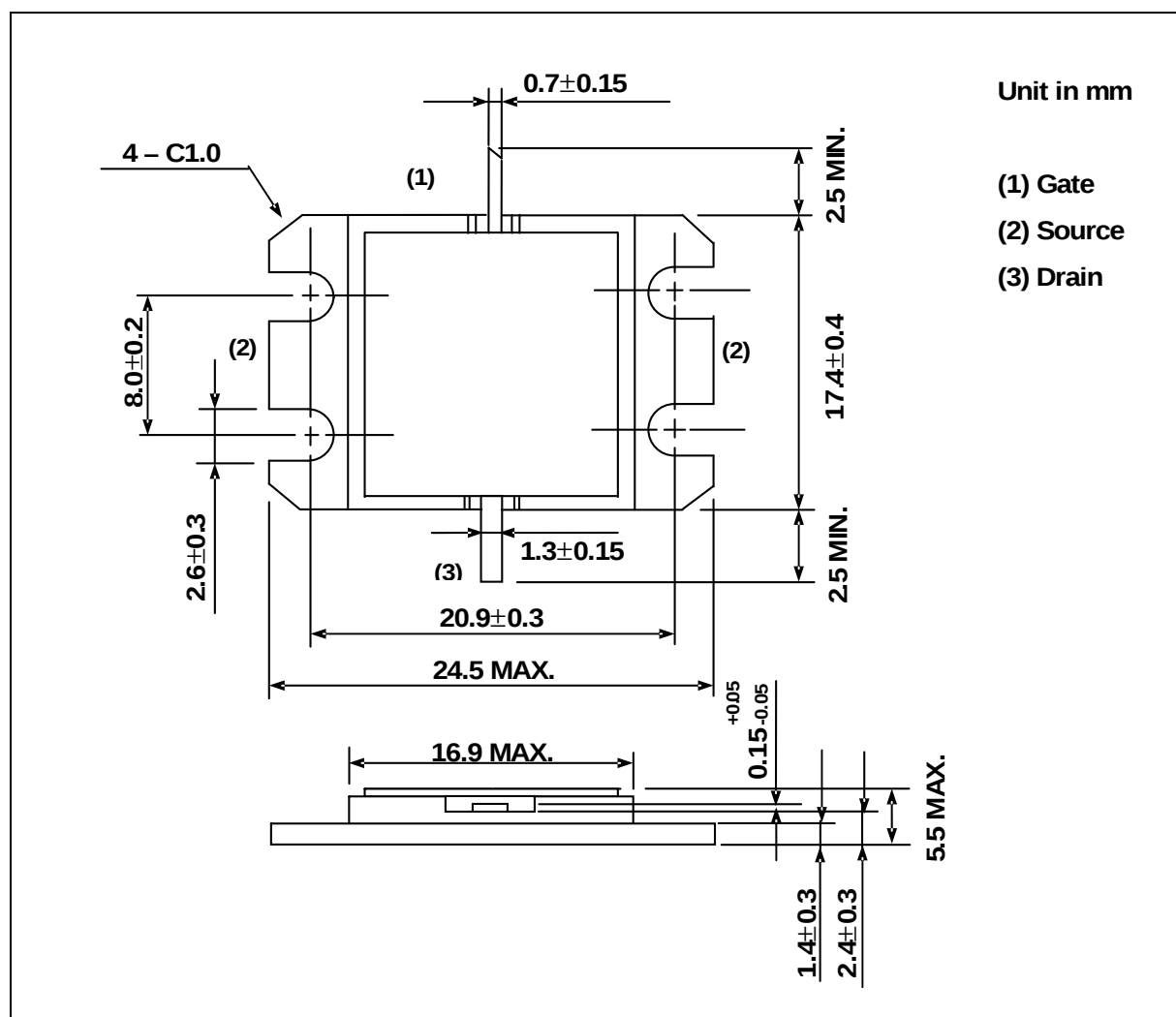
CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 12.0A	S	—	20	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 200mA	V	-1.0	-1.8	-3.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	38	—
Gate-Source Breakdown Voltage	VGSO	IGS= -1.0mA	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	0.5	0.6

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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	V _{DS}	V	15
Gate-Source Voltage	V _{GS}	V	-5
Drain Current	I _{DS}	A	26
Total Power Dissipation (T _c = 25 °C)	P _T	W	250
Channel Temperature	T _{ch}	°C	175
Storage Temperature	T _{stg}	°C	-65 to +175

PACKAGE OUTLINE (7-AA02C)**HANDLING PRECAUTIONS FOR PACKAGE MODEL**

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.